

**isc Silicon NPN Power Transistor**

**2SC2625**

**DESCRIPTION**

- High Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 400V(\text{Min})$
- High Switching Speed
- High Reliability

**APPLICATIONS**

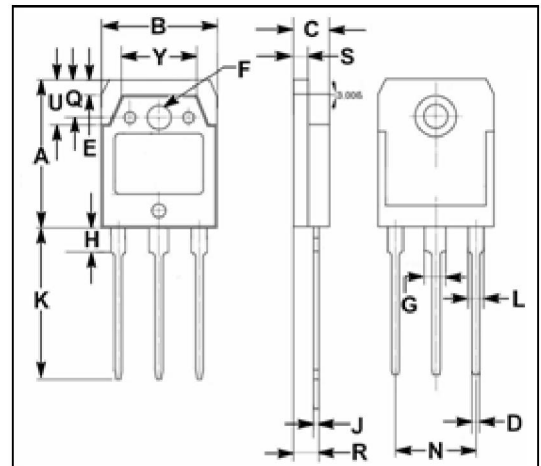
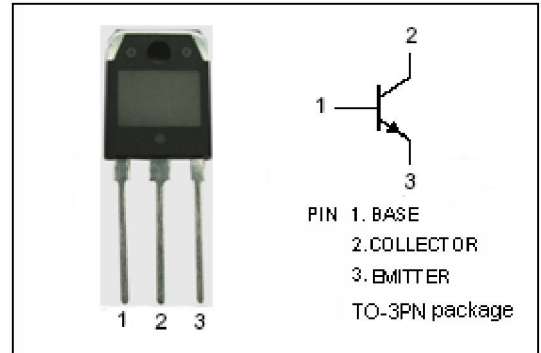
- Switching regulators
- Ultrasonic generators
- High frequency inverters
- General purpose power amplifiers

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	450	V
$V_{CEO}$	Collector-Emitter Voltage	400	V
$V_{CEO(SUS)}$	Collector-Emitter Voltage	400	V
$V_{EBO}$	Emitter-Base voltage	7	V
$I_C$	Collector Current-Continuous	10	A
$I_B$	Base Current-Continuous	3	A
$P_C$	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	80	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.17	$^\circ\text{C/W}$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.38	15.42
C	4.75	4.85
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.98	3.02
H	3.20	3.40
J	0.595	0.605
K	19.95	20.25
L	1.98	2.02
N	10.89	10.91
Q	4.95	5.05
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

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## ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; I_B=0$	400			V
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=1\text{A}; I_B=0$	400			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=1\text{mA}; I_E=0$	450			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=0.1\text{mA}; I_C=0$	7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=4\text{A}; I_B=0.8\text{A}$			1.2	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=4\text{A}; I_B=0.8\text{A}$			1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=450\text{V}; I_E=0$			1.0	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=7\text{V}; I_C=0$			0.1	mA
$h_{FE}$	DC Current Gain	$I_C=4\text{A}; V_{CE}=5\text{V}$	10			

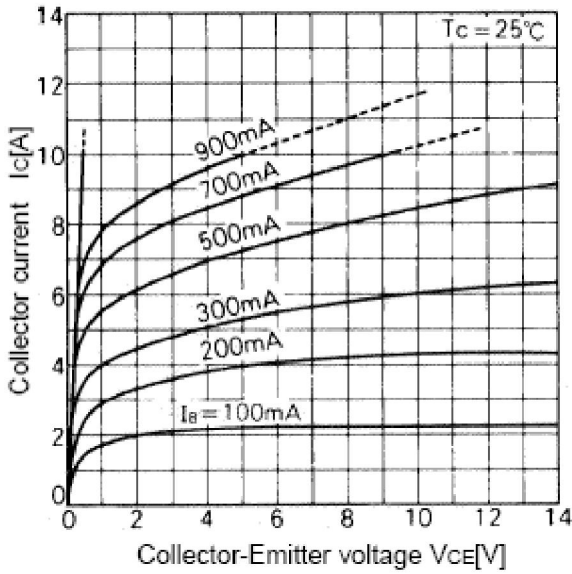
## Switching times

$t_{on}$	Turn-on Time	$I_C=7.5\text{A}, I_{B1}=-I_{B2}=1.5\text{A}$ $R_L=20\Omega; P_W=20\mu\text{s}$ Duty Cycle $\leq 2\%$			1.0	$\mu\text{s}$
$t_{stg}$	Storage Time				2.0	$\mu\text{s}$
$t_f$	Fall Time				1.0	$\mu\text{s}$

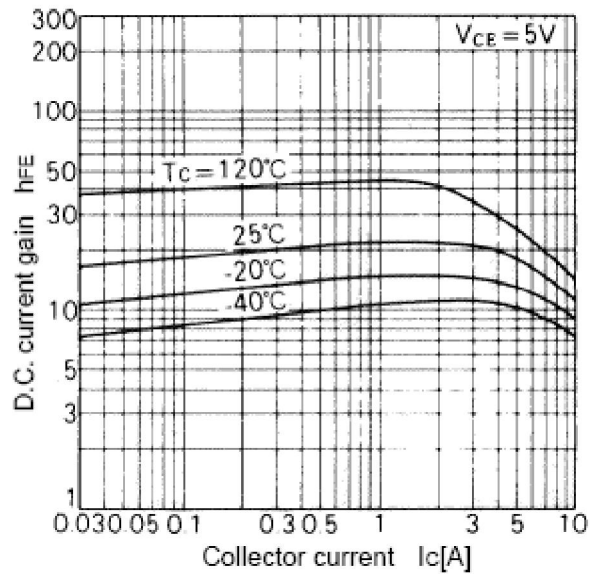
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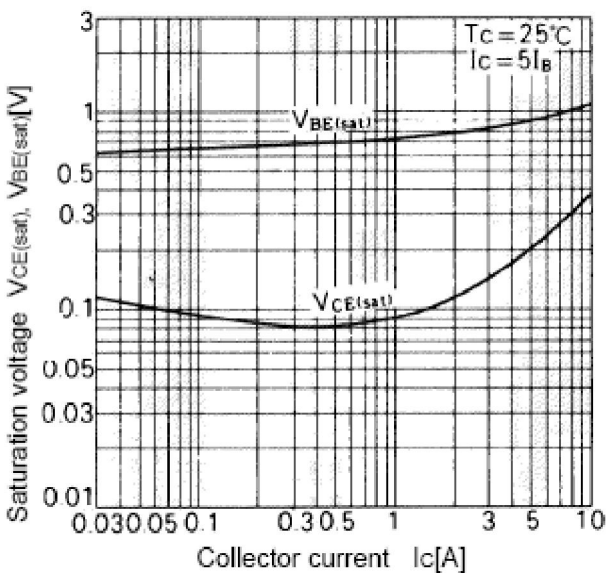
**$I_c$ - $V_{CE}$  Characteristics**



**$h_{FE}$ - $I_c$  Characteristics**



**$V_{CE(sat)}$ - $I_c$  &  $V_{BE(sat)}$ - $I_c$  Characteristics**



**Safe Operating Area**

